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Remarks:

Claims 1-6 remain in the application. Claim 3 has been amended in order to more clearly define the invention of the instant application.

On page 12, line 4 of the specification, the text "- metallization layer 5" has been inserted after the word "lead 9" in order to describe the invention more clearly.

The preliminary amendment is being filed in an effort to comply with the requirement that every feature in the claims should be shown in the drawings or otherwise should be deleted.

An earlier action on the merits is requested.

Respectfully submitted,



For Applicant

YHC:cgm

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Applic. No. 023,189

Marked-Up Version of the Amended Paragraphs in the
Specification and Marked-Up Version of the Amended Claims:

The paragraph starting on page 12, line 1 and ending on
page 12, line 11 now reads as:

In the case of the switching element 6 adjacent alongside on
the right, the current path is produced from top to bottom in
exactly the reverse order: the second supply potential 12 at
the load current connection element 10 - the lead 9 - the
metallization layer 5 - the drain contact of the semiconductor
switch 17 - the source contact of the semiconductor switch 17
- the bonding connection 16, the metallization layer 5 - the
drain contact of the semiconductor switch 17' - the source
contact of the semiconductor switch 17' - the lead 9 - the
load current connection element 10, connected to the first
supply potential 11 (reference-ground potential).

Claim 3(amended). The semiconductor component according to
claim 1, wherein each of said two switching elements contain
two semiconductor switches connected in series [at a junction
point, said junction point], each of said two semiconductor
switches is connected to one of said external load current
connection elements and forms an output of the semiconductor
component.